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Yb³⁺ and Tm³⁺ doped KGd_xLu_yY_{1-x-y}(WO₄)₂ Channel Waveguide Lasers

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Abstract: Channel waveguides with high refractive-index contrast are fabricated in double tungstates. Yb³⁺ lasers with 71% slope efficiency and 418 mW output power are demonstrated. Tm³⁺ lasers at 1843 nm have also been demonstrated. **OCIS codes:** (140.3615) Lasers, Ytterbium; (230.7380) Waveguides, channeled

1. Introduction

In the coming years, many applications in photonics will take advantage of miniaturization by on-chip integration of optical components. In most applications, high-performance integrated lasers are required that provide high output power and efficiency, excellent beam quality, broad wavelength selectivity and tunability, ultrashort pulses, ultranarrow bandwidth, or ultra-low heat generation, potentially by applying a low-cost, straight-forward fabrication process.

The potassium double tungstates KGd(WO₄)₂, KY(WO₄)₂, and KLu(WO₄)₂ are excellent candidates for solidstate lasers [1] because of their high refractive index of ~2.0-2.1 and the large transition cross-sections of rare-earth (RE) ions doped into these hosts. These advantages have been exploited to demonstrate planar [2, 3, 4] and channel [5, 6] waveguide lasers. Co-doping of grown KY(WO₄)₂:RE thin films with Gd and Lu ions for lattice matching and enhanced refractive index contrast of up to 7.5×10^{-3} with respect to the undoped KY(WO₄)₂ substrate [7] has enabled waveguide lasers with tight pump and laser mode confinement of ~10 µm², resulting in excellent slope efficiencies in Yb-doped planar and microstructured channel waveguide lasers of 82.3% [8] and 62% [9], respectively. In this work we demonstrate channel waveguide lasers activated with Yb³⁺ or Tm³⁺ ions.

2. Waveguide Fabrication

The composition of the active layer was chosen to provide the maximum refractive index contrast and simultaneously minimal lattice mismatch with the KY(WO₄)₂ substrate. The lattice parameters of the monoclinic layer in the three crystallographic axes were calculated as weighted averages of the lattice parameters of the stoichiometric compositions KGd(WO₄)₂, KLu(WO₄)₂, and KYb(WO₄)₂ and were matched to the parameters of the KY(WO₄)₂ substrate, see Fig. 1. In the extreme case, no Y³⁺ was incorporated in the active layer in order to achieve a maximal refractive index contrast of 1.5% between layer and substrate [10]. A KGd_{0.49}Lu_{0.485}Yb_{0.025}(WO₄)₂ layer was grown by liquid phase epitaxy onto a (010)-orientated KY(WO₄)₂ substrate. Subsequently, the layer was microstructured by Ar⁺ beam milling [9] to obtain ridge waveguides along the N_g optical axis. The structure was overgrown by an epitaxial layer of KY(WO₄)₂, resulting in buried channel waveguides.



Fig. 1. Lattice mismatch (color) of $KGd_xLu_yY_{1-x-y}(WO_4)_2$ waveguides with decreasing Y concentration (black lines) on b-oriented $KY(WO_4)_2$ substrates for the lattice the *a*-axis (a) and *c*-axis (b) and resulting refractive-index increase (white lines).

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3. Laser Performance

In the case of Yb³⁺, pump light at 981 nm from a Ti:sapphire laser was end-coupled into the waveguide. The light outcoupled at the other end of the waveguide was collimated and directed to a powermeter or a spectrometer. At the input side a dielectric mirror with a high transmission of 96% for the pump light and a high reflectivity of 99.8% for the laser light was directly butt-coupled to the endfacet. An outcoupling mirror with $T_{out} = 70\%$ at 1023 nm was attached to the other side. We obtained a maximum laser output power of 418 mW at 1023 nm, limited only by the available pump power, with a slope efficiency of 71% versus launched pump power; see Fig. 2a. The threshold was 40 mW.

In the case of Tm^{3+} , lower refractive-index contrast and small Tm^{3+} doping of 1at.% was chosen for the first laser tests. pump light at 800 nm from a Ti:sapphire laser was end-coupled into the waveguide. Currently, more than 2 mW of output power at 1843 nm has been achieved. Improvements of pump and laser mode confinement by reducing the Y³⁺ content of the layer as well as higher Tm^{3+} concentration in order to exploit the cross-relaxation typically observed in Tm^{3+} compounds for improving the quantum efficiency of the laser will lead to significantly higher output powers also in this case, and related work is in progress.



Fig. 2. Input-output curves of $KGd_xLu_yY_{1-x-y}(WO_4)_2$ channel waveguide lasers (a) doped with Yb^{3+} at 1023 nm and (b) doped with Tm^{3+} at 1843 nm.

4. Conclusion

The remarkable performance of such rare-earth-ion-doped, microstructured channel waveguide lasers makes them excellent candidates for high-repetition-rate ultrashort-pulse generation on a chip, diode-array side-pumped channel waveguide lasers, and ultra-narrow-linewidth distributed feedback waveguide lasers.

5. References

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